

AMENDMENTS TO THE CLAIMS

Claims 1-51 (Canceled)

Claim 52 (Currently Amended): A method of treating a dielectric film comprising:
etching a portion of said dielectric film so as to form in said dielectric film a sidewall surface; and
exposing said sidewall surface to at least one of TMCTS and OMCTS in a non-plasma environment, wherein
said dielectric film has a dielectric constant value less than the dielectric constant of SiO₂.

Claim 53 (Canceled)

Claim 54 (Previously Presented): The method according to Claim 52, further comprising
forming a mask on said dielectric film; and
forming a pattern in said mask, wherein
said etching comprises transferring said pattern in said mask to said dielectric film.

Claim 55 (Previously Presented): The method according to Claim 52, further comprising exposing said sidewall surface to at least one of a nitrogen containing material and a chlorine containing material.

Claim 56 (Previously Presented): The method according to Claim 52, wherein said dielectric film has a dielectric constant in a range of from 1.6 to 2.7.

Claim 57 (Previously Presented): The method according to Claim 52, wherein said dielectric film is porous.

Claim 58 (Previously Presented): The method according to Claim 52, wherein said dielectric film is non-porous.

Claim 59 (Previously Presented): The method according to Claim 52, further comprising heating said dielectric film to a temperature in a range of from 50C to 400C.

Claim 60 (Previously Presented): The method according to Claim 52, wherein said sidewall surface is exposed to TMCTS.

Claim 61 (Previously Presented): The method according to Claim 52, wherein said sidewall surface is exposed to OMCTS.

Claim 62 (New): The method according to Claim 52, further comprising exposing said sidewall surface to a chlorine containing material.

Claim 63 (New): The method according to Claim 62, wherein said sidewall surface is simultaneously exposed to the chlorine containing material and to the at least one of TMCTS and OMCTS.